



1N60P

Power MOSFET

1.2A, 600V N-CHANNEL POWER MOSFET

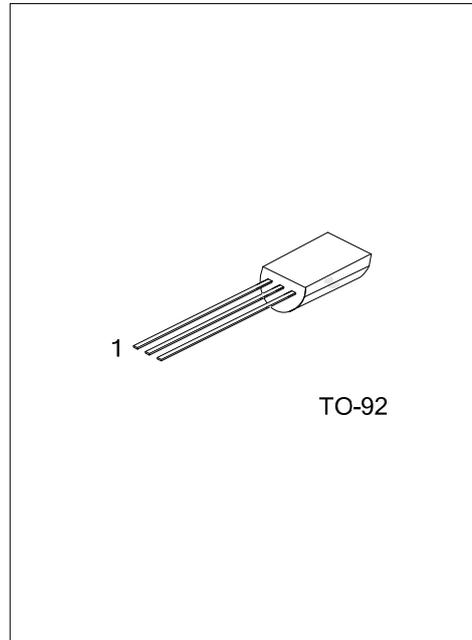
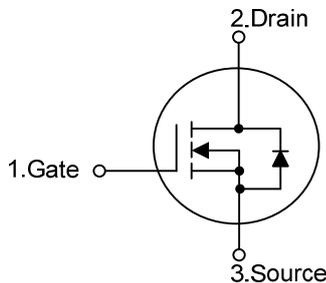
DESCRIPTION

The UTC **1N60P** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristic. This power MOSFET is usually used at high speed switching applications of power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \leq 11.5 \Omega @ V_{GS}=10V, I_D=0.6A$
- * Ultra Low gate charge (typical 5.0nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 3.0 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



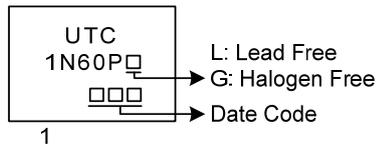
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1N60PL-T92-B	1N60PG-T92-B	TO-92	G	D	S	Tape Box
1N60PL-T92-K	1N60PG-T92-K	TO-92	G	D	S	Bulk
1N60PL-T92-R	1N60PG-T92-R	TO-92	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N60PG-T92-B</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) B: Tape Box, K: Bulk (2) T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	600	V
Gate-Source Voltage	V_{GSS}	± 30	V
Avalanche Current (Note 2)	I_{AR}	1.2	A
Continuous Drain Current	I_D	1.2	A
Pulsed Drain Current (Note 2)	I_{DM}	4.8	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	50
	Repetitive (Note 2)	E_{AR}	4.0
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

- Notes:
1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature
 3. $L = 60\text{mH}$, $I_{AS} = 1\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
 4. $I_{SD} \leq 1.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	140	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified.)

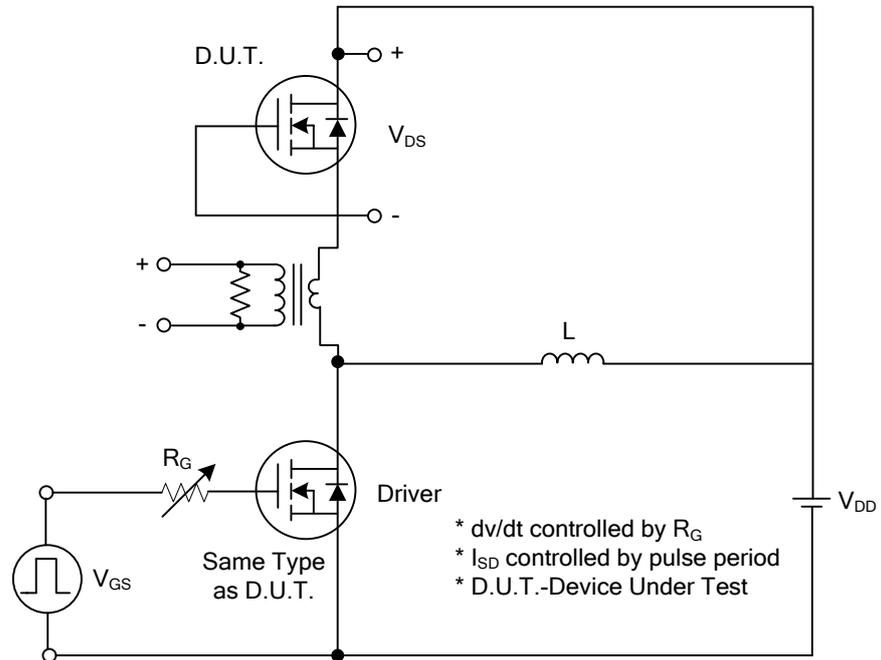
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS} V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA		0.4		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =0.6A		9.3	11.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		120	150	pF
Output Capacitance	C _{OSS}			20	25	pF
Reverse Transfer Capacitance	C _{RSS}			3.0	4.0	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =300V, I _D =1.2A, R _G =50Ω (Note 2, 3)		5	20	ns
Turn-On Rise Time	t _R			25	60	ns
Turn-Off Delay Time	t _{D(OFF)}			7	25	ns
Turn-Off Fall Time	t _F			25	60	ns
Total Gate Charge	Q _G	V _{DS} =480V, V _{GS} =10V, I _D =1.2A (Note 2, 3)		5.0	6.0	nC
Gate-Source Charge	Q _{GS}			1.0		nC
Gate-Drain Charge	Q _{GD}			2.6		nC
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1.2A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				1.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				4.8	A
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =1.2A		160		ns
Reverse Recovery Charge	Q _{RR}	dI _F /dt=100A/μs (Note 1)		0.3		μC

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

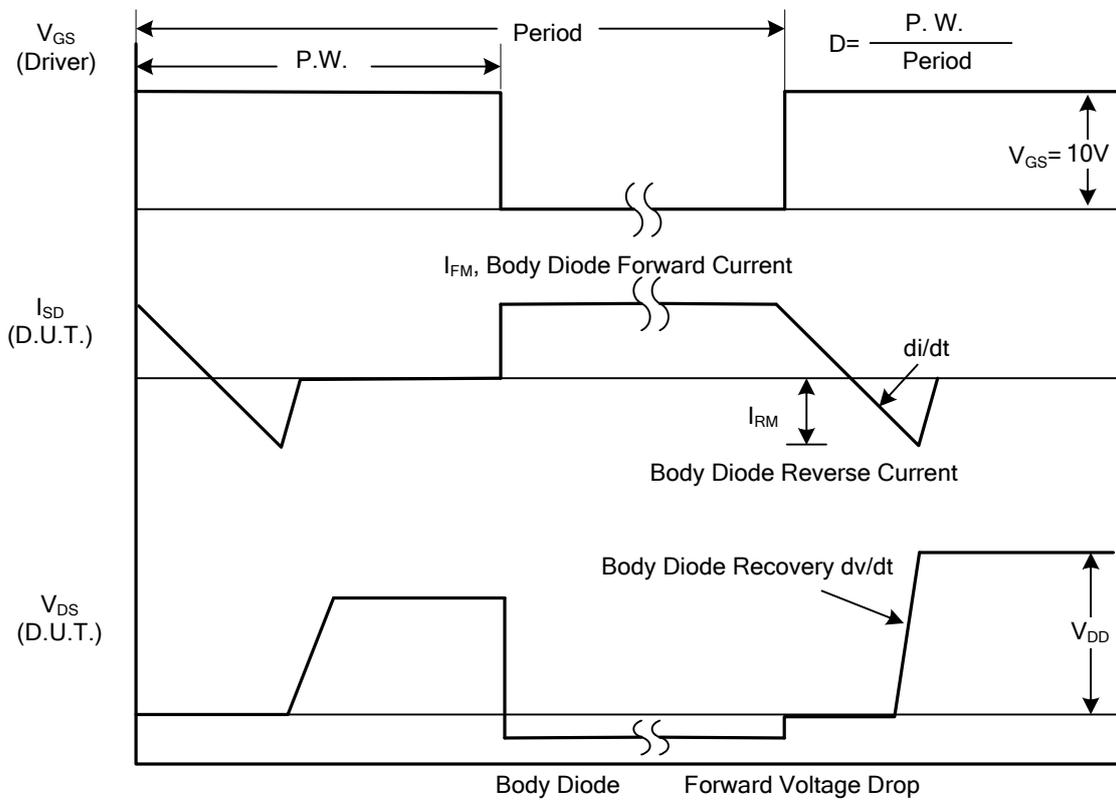
2. Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%

3. Essentially Independent of Operating Temperature

TEST CIRCUITS AND WAVEFORMS

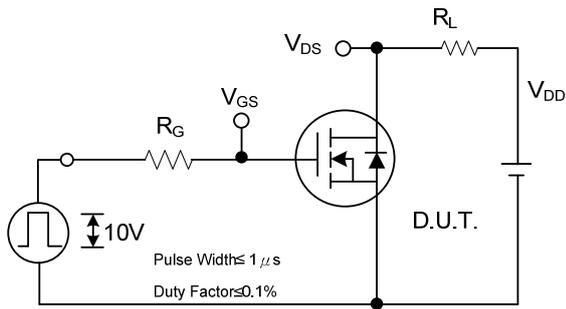


Peak Diode Recovery dv/dt Test Circuit

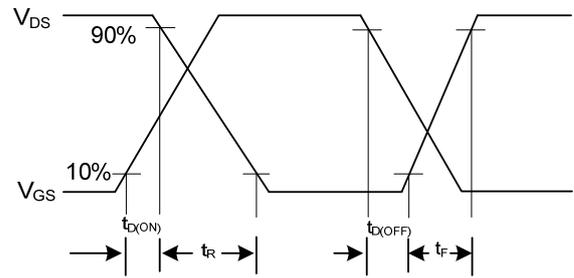


Peak Diode Recovery dv/dt Waveforms

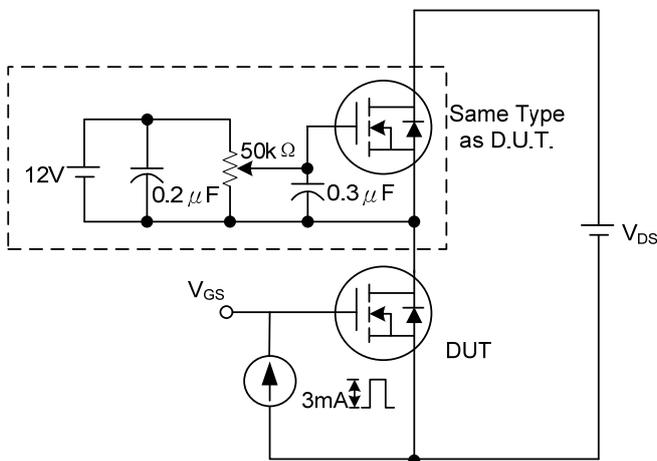
TEST CIRCUITS AND WAVEFORMS (Cont.)



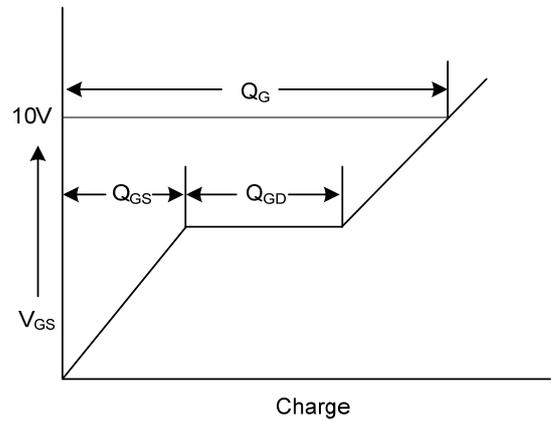
Switching Test Circuit



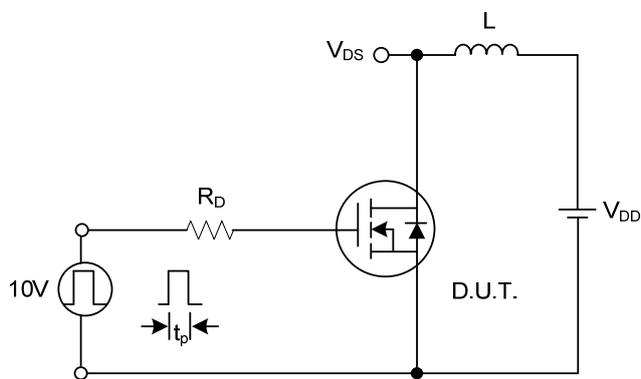
Switching Waveforms



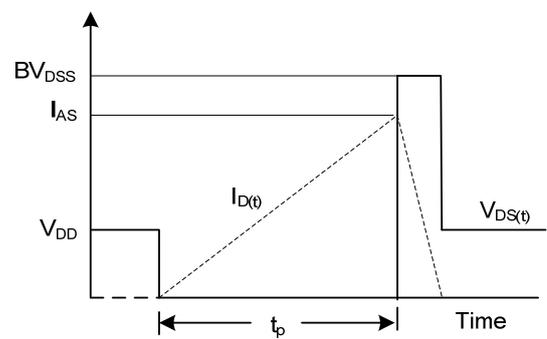
Gate Charge Test Circuit



Gate Charge Waveform

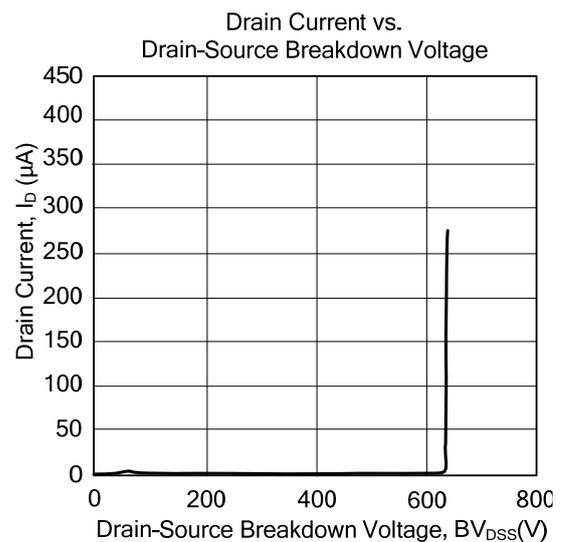
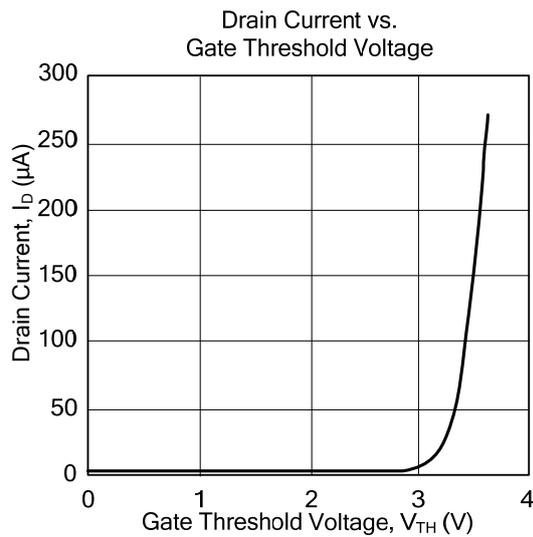
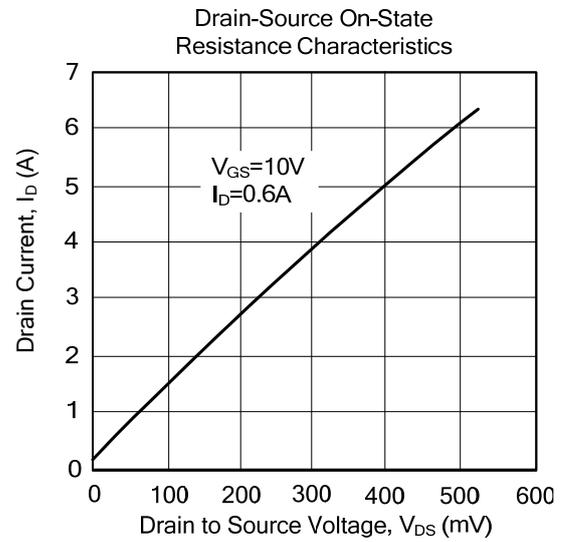
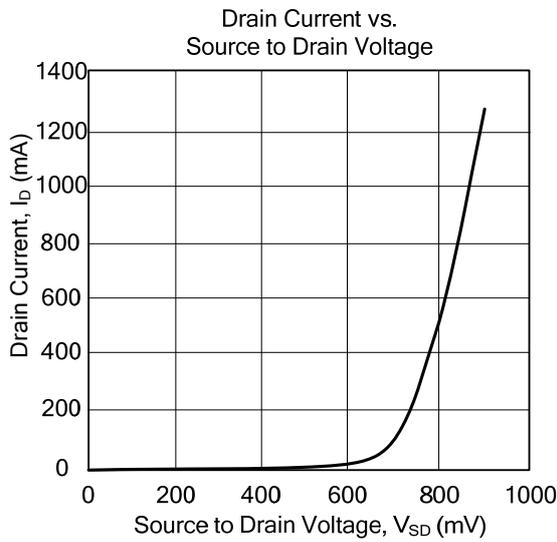


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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